NEC

MOS INTEGRATED CIRCUIT $\mu PD166005$

SINGLE N-CHANNEL HIGH SIDE INTELLIGENT POWER DEVICE

DESCRIPTION

The μ PD166005 is N-channel high side driver with charge pump, diagnostic function, embedded protection functions. When the device is over temperature or over current is generated in output MOS, the protection function operates while the built-in diagnosis output signal is output. In addition, the built-in diagnosis signal is output when open status of the output pin is detected.

FEATURES

- High temperature operation (T_{ch} = 175°C MAX.)
- Built-in charge pump circuit
- Low on-state resistance
- $R_{DS(on)}$ = 100 m Ω MAX. (VIN = VIH, IO = 1.5 A, Tch = 25°C)
- Built-in protection circuit
 - Current limitation
 - Over temperature protection
- Built-in open load detection circuit
- Built-in diagnosis output circuit
- Package: Power SOP 8

ORDERING INFORMATION

Part Number	Lead plating	Packing	Package
μ PD166005GR-E1-AZ ^{Note}	Sn-Bi	Tape 2500 p/reel	Power SOP 8
μ PD166005GR-E2-AZ ^{Note}	Sn-Bi	Tape 2500 p/reel	Power SOP 8

Note Pb-free (This product does not contain Pb in the external electrode.)

QUALITY GRADE

Part Number	Quality Grade
μ PD166005GR-E1-AZ ^{Note}	Special
μ PD166005GR-E2-AZ ^{Note}	Special

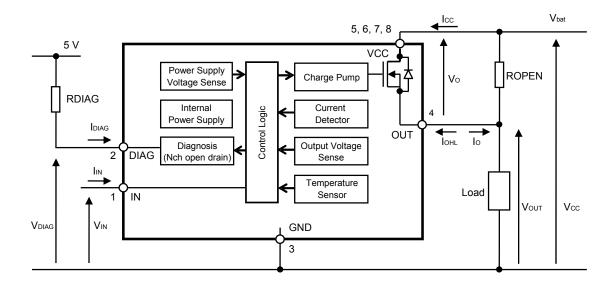
Please refer to "Quality Grades on NEC Semiconductor Devices" (Document No. C11531E) published by NEC Corporation to know the specification of quality grade on the devices and its recommended applications.

APPLICATION

• Switching of types of 14 V loads such as L load, resistance and capacity.

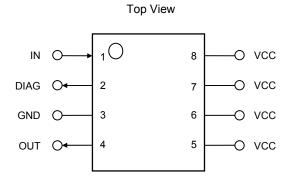
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BLOCK DIAGRAM



PIN CONFIGURATION

Power SOP 8



PIN FUNCTIONS

Pin No.	Pin Name	Function
1	IN	Input pin
2	DIAG	DIAG output pin
3	GND	Ground pin
4	OUT	High side output pin
5	VCC	Power supply pin
6	VCC	Power supply pin
7	VCC	Power supply pin
8	VCC	Power supply pin

Parameter	Symbol	Condition	Rating	Unit
Power supply voltage	Vcc1		–0.3 to +35	V
	Vcc2	Rs = 1 Ω, τ = 250 ms	60	V
Input voltage	VIN		-0.5 to +7.0	V
Input current	lin		±10	mA
Output current	ΙοΑ		2	А
Output negative voltage	Voa		Vcc - 60	V
Power dissipation	PD	T _A = 25°C ^{Note}	1.0	W
Operation temperature	Topt		-40 to +125	°C
Storage temperature	Tstg		–55 to +175	°C
DIAG output voltage	VDIAG		7.0	V
DIAG output current	DIAG		10	mA

ABSOLUTE MAXIMUM RATINGS (TA = 25°C, unless otherwise specified)

Note When mounted on a glass substrate epoxy (where FR-4 is 10 cm x 10 cm, dimension of copper foil is 15% and thickness of copper foil is $35 \mu m$)

Caution Product quality may suffer if the absolute maximum rating is exceeded even momentarily for any parameters. That is, the absolute maximum ratings are rated values at which the product is on the verge of suffering physical damage, and therefore the product must be used under conditions that ensure that the absolute maximum ratings are not exceeded.

The ratings and conditions indicated for DC characteristics and AC characteristics represent the quality assurance range during normal operation.

RECOMMENDED OPERATIONG CONDITIONS (TA = -40°C to +125°C, unless otherwise specified)

Parameter	Symbol	Conditions	MIN.	TYP.	MAX.	Unit
Power supply voltage	Vcc	$V_{IH} = 3 V, V_0 = V_{CC} - 0.4 V (RL = 9.3 \Omega),$	4.5		16	V
		V _{IL} = 1 V, V ₀ = 0.2 V (RL = 9.3 Ω),				
		V _{DIAG} = 0.5 V (I _{DIAG} = 0.6 mA)				
Input voltage	VIH	Vcc = 4.5 to 16 V	3		7.0	V
	V⊫		0		1.0	V
Output current	Іоа	Vcc = 8 to 16 V	0		1.5	А
DIAG output voltage	VDIAG		0		7.0	V
DIAG output current	DIAG		0		0.6	mA

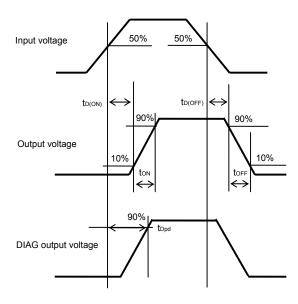
Parameter	Symbol	Conditions	S	MIN.	TYP.	MAX.	Unit
Input voltage	VIH	Vcc = 4.5 to 16 V		3		7.0	V
in par rollago	VIL			0		1.0	V
Input current	Ін	V _{IN} = 5.5 V		30		400	μA
	lı.	$V_{IN} = 0 V$		-10			μA
Standby current Note1	Іссн	VIN = VIH				4	, mA
	Iccl	VIN = VIL				0.2	mA
Output leakage current	Іон1	VIN = VIL, VO = VCC				2000	μA
	Іон2	VIN = VIL, VO = 4 V				400	μA
	IOL	$V_{IN} = V_{IL}, V_O = 0 V$		-240			μA
DIAG output low level voltage	VDIAG	Vcc = 4.5 to 16 V, IDIAG =	0.6 mA			0.5	V
DIAG output leakage current	DIAG	V _{DIAG} = 7.0 V				10	μA
Open load detection	Voih	VIN = 0 V, VDIAG changing	$V_{IN} = 0 V, V_{DIAG}$ changing point (L \rightarrow H)				V
Load connection detection	Voil	$V_{IN} = 0 V, V_{DIAG}$ changing point (H \rightarrow L)				1.45	V
Drain to source on-state	RDS(on)	VIN = VIH, IO = 1.5 A	T _{ch} = 25°C		80	100	mΩ
resistance			T _{ch} = 150°C		150	180	mΩ
Over current detection Note2	ls			2		(10)	А
Over temperature detection Note2	Tth			(175)			°C
Turn on delay time	t _{D(ON)}	RL = 9.3 Ω, Vcc = 14 V			5	50	μs
Turn off delay time	td(OFF)				50	200	μs
Rise time	t on				30	200	μs
Fall time	toff				20	200	μs
DIAG output delay time	tDpd	RL = 13 Ω, Vcc = 14 V				200	μs
Negative output voltage	–Vo	Io = -60 mA				Vcc - 50	V
Output oscillation cycle at over current condition	ts	Over current				14	ms
Output on duty at over current condition	Ds					30	%

ELECTRICAL SPECIFICATIONS (Vcc = 8 to 16 V, Tch = -40 to +175°C, unless otherwise specified)

Notes 1. OUT current and DIAG current are not included.

2. () is a reference value.

MEASUREMENT CONDITION



TRUTH TABLE

Parameter	Vin	Vout	VDIAG
Normal operation	Н	Н	Н
	L	L	L
Over temperature detection	Н	L	L
	L	L	L
Over current detection	Н	Chopping	L
	L	L	L
Open load detection	Н	Н	н
	L	Н	Н

OUTLINE OF FUNCTIONS

Pre-Driver (Charge Pump Circuit) ON/OFF Control

When the input voltage of the input pin (IN) is high level (3.0 V or more), the output MOS (Nch) turns on. When the output voltage of the input pin (IN) is low level (1.0 V or less), the output MOS (Nch) turns off. Charge pump circuit is built-in to drive the output MOS (Nch) that is connected to the high side.

Over Current Detection Circuit

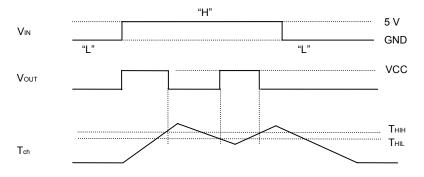
This circuit detects over current to output pin (OUT) caused by short circuit etc., and feeds back detection signal to control circuit.

When the over current is detected, the current limitation circuit and the control circuit start operation. The output current is restricted and chopping operation begins. The DIAG output is low level at this time.

Over temperature Detection Circuit

This circuit detects over temperature by output MOS (Nch) driving, and feeds back detection signal to control circuit.

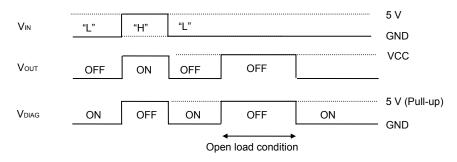
When the circuit detects over temperature, the protection function of the control circuit operates and output is shutdown. Output MOS (Nch) automatically restarts when channel temperature cools down after shutdown.



Open Load Detection Circuit

This circuit detects connection/open load of output pin (OUT) when OFF (VIN = VIL).

When using the open load detection function, pull-up the output pin (OUT) to Vcc. (Recommended value: $5.1 \text{ k}\Omega \pm 10\%$) Open load is detected by inputting low level input voltage (1.0 V or less) to input pin (IN). DAIG pin outputs Hi-Z (pull-up: high level) when the output pin is open.

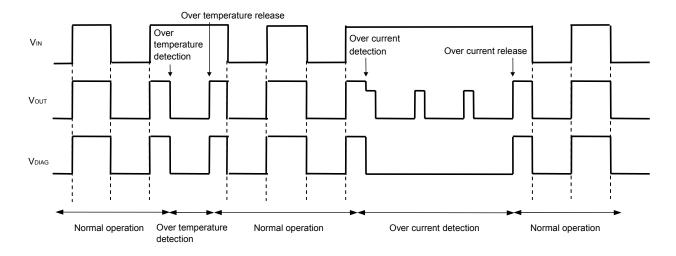


Remark The pull-up resistance does not affect other circuits and electronic characteristics.

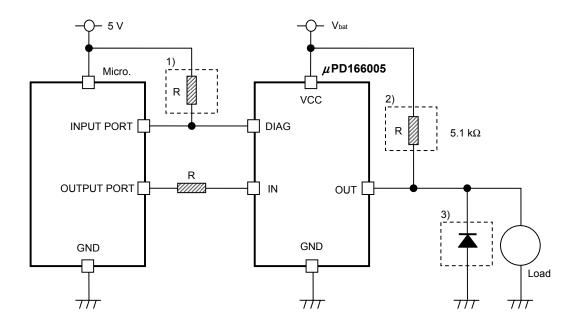
Diagnostic Output Circuit

This circuit controls output of diagnosis signal form DIAG pin when Over current or Over temperature or Open load is detected.

TIMING CHART



EXAMPLE OF APPLICATION CIRCUIT



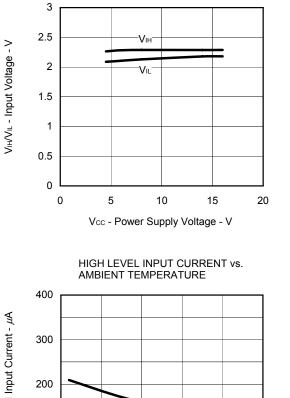
Cautions 1. DIAG pin is Nch open drain structure. When using diagnostic function, pull-up DIAG pin to 5 V. (power supply lines such as Microcomputer)

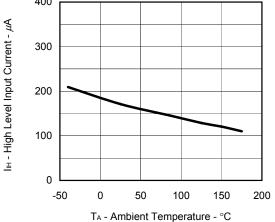
- When using Open load detection function, Pull-up OUT pin to Vcc. (Recommended value: 5.1 kΩ±10%) (The pull-up resistance does not affect other circuits and electronic characteristics.)
- 3. If output load voltage exceeds Vcc 50 V when L load is driven, it is necessary to protect this product with an external rectifying diode or zener diode.
- 4. This circuit diagram is shown as an example of connection, and is not intended for mass production design.

TYPICAL CHARACTERISTICS

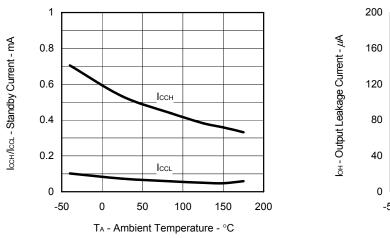
INPUT VOLTAGE vs. POWER SUPPLY VOLTAGE

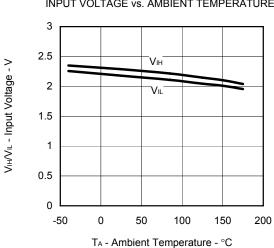
INPUT VOLTAGE vs. AMBIENT TEMPERATURE



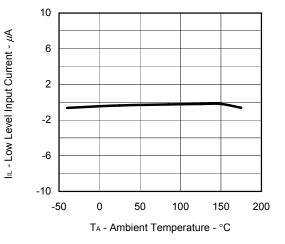


STUNDBY CURRENT vs. AMBIENT TEMPERATURE

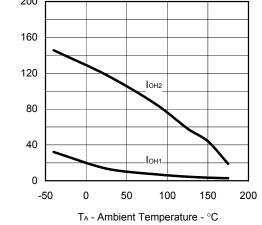


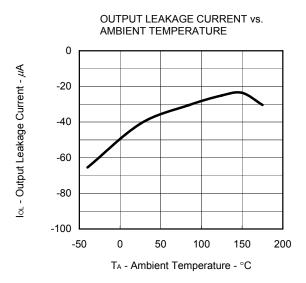


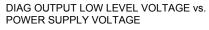
LOW LEVEL INPUT CURRENT vs. AMBIENT TEMPERATURE

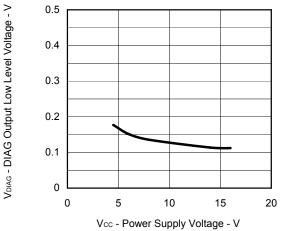


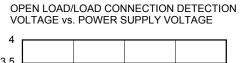


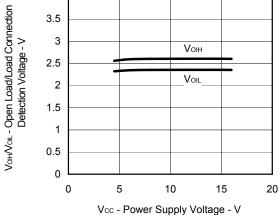






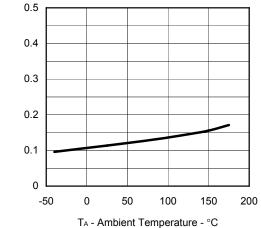




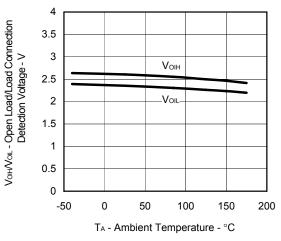


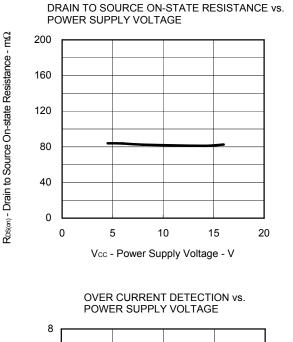


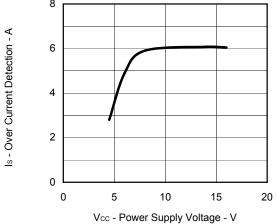
DIAG OUTPUT LOW LEVEL VOLTAGE vs. AMBIENT TEMPERATURE



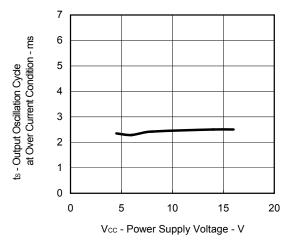
OPEN LOAD / LOAD CONNECTION DETECTION VOLTAGE vs. AMBIENT TEMPERATURE

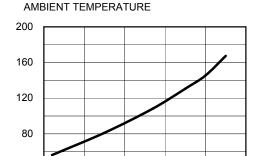






OUTPUT OSCILLATION CYCLE AT OVER CURRENT CONDITION vs. POWER SUPPLY VOLTAGE





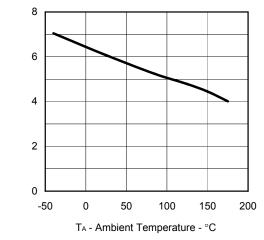
DRAIN TO SOURCE ON-STATE RESISTANCE vs.

40 0 -50 0 50 100 150 200 TA - Ambient Temperature - °C

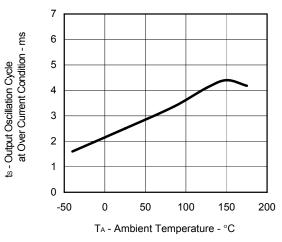
 $R_{\text{DS}(\text{on})}$ - Drain to Source On-state Resistance - $m\Omega$

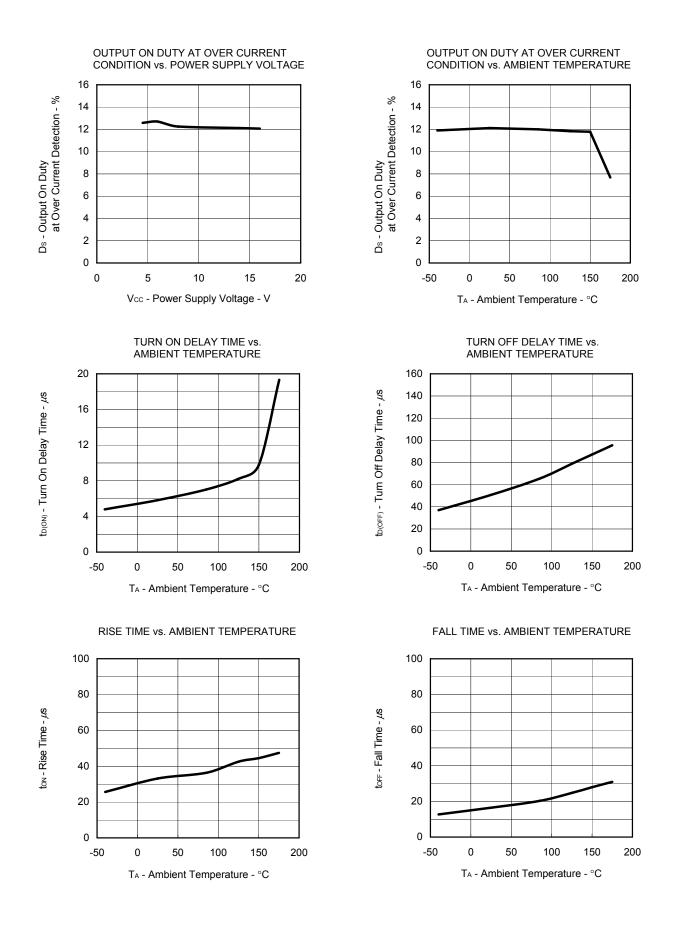
Is - Over Current Detection - A

OVER CURRENT DETECTION vs. AMBIENT TEMPERATURE

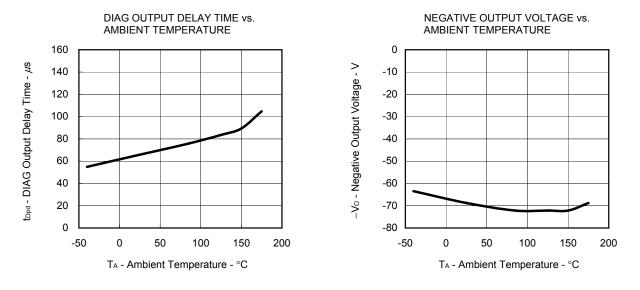


OUTPUT OSCILLATION CYCLE AT OVER CURRENT CONDITION vs. AMBIENT TEMPERATURE

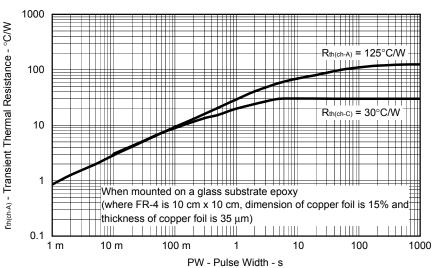






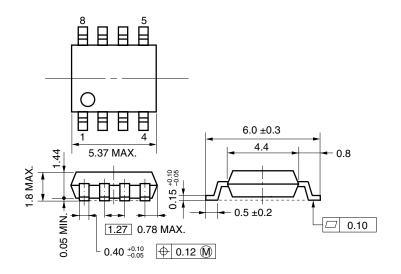






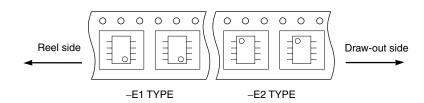
TRANSIENT THERMAL RESISTANCE vs. PULSE WIDTH

PACKAGE DRAWING



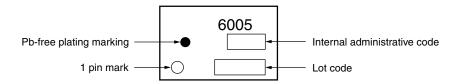
TAPE INFORMATION

There are two types (-E1, -E2) of taping depending on the direction of the device.



MARKING INFORMATION

This figure indicates the marking items and arrangement. However, details of the letterform, the size and the position aren't indicated.



RECOMMENDED SOLDERING CONDITIONS

The μ PD166005 should be soldered and mounted under the following recommended conditions.

For soldering methods and conditions other than those recommended below, contact an NEC Electronics sales representative.

For technical information, see the following website.

Semiconductor Device Mount Manual (http://www.necel.com/pkg/en/mount/index.html)

• µPD166005GR-E1-AZ ^{Note}: Power SOP 8

• µPD166005GR-E2-AZ ^{Note}: Power SOP 8

Process	Conditions	Symbol
Infrared reflow	Maximum temperature (package's surface temperature): 260°C or below,	IR60-00-3
	Time at maximum temperature: 10 seconds or less,	
	Time at temperature higher than 220°C: 60 seconds or less,	
	Preheating time at 160°C to 180°C: 60 to 120 seconds, Times: Three times,	
	Flux: Rosin flux with low chlorine (0.2 Wt% or below) recommended.	
Partial Heating Method	Pin temperature: 300°C or below,	-
	Heat time: 3 seconds or less (Per each side of the device),	
	Flux: Rosin flux with low chlorine (0.2 Wt% or below) recommended.	

Note Pb-free (This product does not contain Pb in the external electrode.)

- NOTES FOR CMOS DEVICES ——

(1) VOLTAGE APPLICATION WAVEFORM AT INPUT PIN

Waveform distortion due to input noise or a reflected wave may cause malfunction. If the input of the CMOS device stays in the area between V_{IL} (MAX) and V_{IH} (MIN) due to noise, etc., the device may malfunction. Take care to prevent chattering noise from entering the device when the input level is fixed, and also in the transition period when the input level passes through the area between V_{IL} (MAX) and V_{IH} (MIN).

(2) HANDLING OF UNUSED INPUT PINS

Unconnected CMOS device inputs can be cause of malfunction. If an input pin is unconnected, it is possible that an internal input level may be generated due to noise, etc., causing malfunction. CMOS devices behave differently than Bipolar or NMOS devices. Input levels of CMOS devices must be fixed high or low by using pull-up or pull-down circuitry. Each unused pin should be connected to VDD or GND via a resistor if there is a possibility that it will be an output pin. All handling related to unused pins must be judged separately for each device and according to related specifications governing the device.

③ PRECAUTION AGAINST ESD

A strong electric field, when exposed to a MOS device, can cause destruction of the gate oxide and ultimately degrade the device operation. Steps must be taken to stop generation of static electricity as much as possible, and quickly dissipate it when it has occurred. Environmental control must be adequate. When it is dry, a humidifier should be used. It is recommended to avoid using insulators that easily build up static electricity. Semiconductor devices must be stored and transported in an anti-static container, static shielding bag or conductive material. All test and measurement tools including work benches and floors should be grounded. The operator should be grounded using a wrist strap. Semiconductor devices must not be touched with bare hands. Similar precautions need to be taken for PW boards with mounted semiconductor devices.

④ STATUS BEFORE INITIALIZATION

Power-on does not necessarily define the initial status of a MOS device. Immediately after the power source is turned ON, devices with reset functions have not yet been initialized. Hence, power-on does not guarantee output pin levels, I/O settings or contents of registers. A device is not initialized until the reset signal is received. A reset operation must be executed immediately after power-on for devices with reset functions.

5 POWER ON/OFF SEQUENCE

In the case of a device that uses different power supplies for the internal operation and external interface, as a rule, switch on the external power supply after switching on the internal power supply. When switching the power supply off, as a rule, switch off the external power supply and then the internal power supply. Use of the reverse power on/off sequences may result in the application of an overvoltage to the internal elements of the device, causing malfunction and degradation of internal elements due to the passage of an abnormal current.

The correct power on/off sequence must be judged separately for each device and according to related specifications governing the device.

(6) INPUT OF SIGNAL DURING POWER OFF STATE

Do not input signals or an I/O pull-up power supply while the device is not powered. The current injection that results from input of such a signal or I/O pull-up power supply may cause malfunction and the abnormal current that passes in the device at this time may cause degradation of internal elements. Input of signals during the power off state must be judged separately for each device and according to related specifications governing the device.

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